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### JP6036966A2: THIN FILM CAPACITOR

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Kind:

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Abstract: **Purpose:** To obtain a thin film capacitor capable of further improving electric characteristics determined from the characteristics of a polymer layer formed as dielectric substance by a vapor deposition polymerization method.

**Constitution:** A thin film capacitor 1 is provided with a substrate 2 on which multilayered structure 5 constituted of film type inner electrodes 3a, 3b, 3c and film type dielectric substance 4a, 4b is formed. The dielectric substance 4a, 4b is composed of a polymer film of phloroalkylated aromatic polyimide containing N-methylacrididium-7,7,8,8-tetracyanoquino dimethane complex (which is called 'TCNQ complex' hereafter). The polymer film of phloroalkylated aromatic polyimide containing the TCNQ complex is formed by a vapor deposition polymerization method applying the following to evaporation source material; monomer of 2-2 bis (4-aminophenyl) hexaphloropropane, monomer of pyromellitic dihydride and crystal of TCNQ complex.

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Other Abstract Info: **DERABS C94-087082 DERC94-087082**

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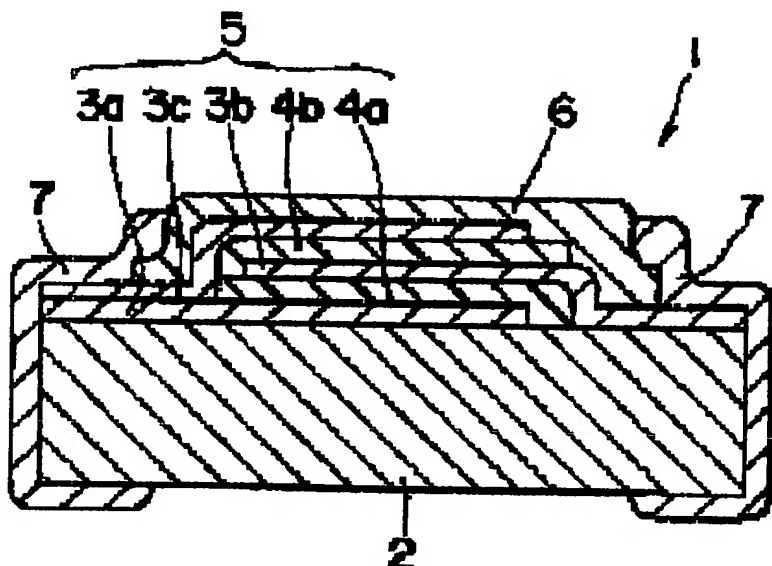
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### (54) THIN FILM CAPACITOR

(57) Abstract:

**PURPOSE:** To obtain a thin film capacitor capable of further improving electric characteristics determined from the characteristics of a polymer layer formed as dielectric substance by a vapor deposition polymerization method.

**CONSTITUTION:** A thin film capacitor 1 is provided with a substrate 2 on which multilayered structure 5 constituted of film type inner electrodes 3a, 3b, 3c and film type dielectric substance 4a, 4b is formed. The dielectric substance 4a, 4b is composed of a polymer film of phloroalkylated aromatic polyimide containing N-methylacridimium-7,7,8,8-tetracyanoquinodimethane complex (which is called 'TCNQ complex' hereafter). The polymer film of phloroalkylated aromatic polyimide containing the TCNQ complex is formed by a vapor deposition polymerization method applying the following to evaporation source material; monomer of 2-2 bis (4-aminophenyl) hexaphloropropane,



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